

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-30V	6.4m Ω @-10V	-16A
	8.3m Ω @-4.5V	

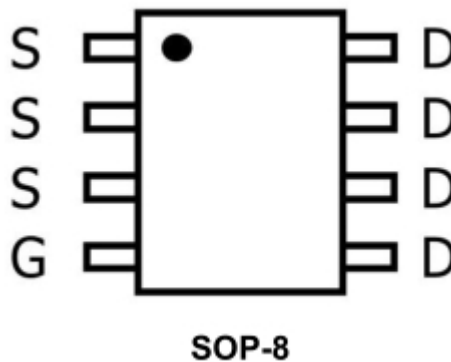
Feature

- $V_{DS} = -30V, I_D = -16A, R_{DS(ON)} < 8m\Omega @ V_{GS} = -10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package.

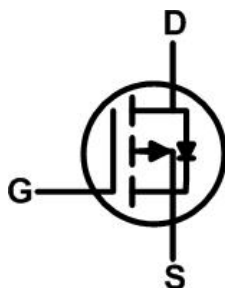
Application

- Power management
- Load switch

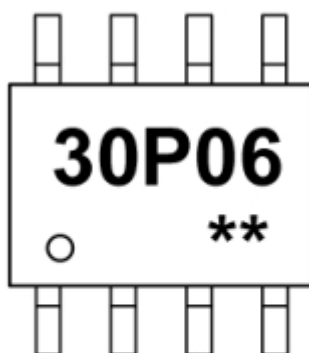
Package



Circuit diagram



Marking



30P06 =Device Code
****** =Week Code

Absolute maximum ratings

($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-16	A
Drain Current-Pulsed ¹	I_{DM}	-64	A
Maximum Power Dissipation	P_D	3.5	W
Thermal Resistance,Junction-to-Ambient ²	$R_{\theta JA}$	36	$^{\circ}\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}\text{C}$

Electrical characteristics

($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V _{GS} = 0V, I _D = -250μA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V			-1	uA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	uA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250μA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -15A		6.4	8	mΩ
		V _{GS} = -4.5V, I _D = -10A		8.3	13	
		V _{DS} = -10V, I _D = -15A	30			
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} =0V, f=1MHz		3500		pF
Output Capacitance	C _{oss}			486		
Reverse Transfer Capacitance	C _{rss}			340		
Switching Characteristics						
Turn-on Delay Time	T _{d(on)}	V _{DD} = -15V, , I _D = -10A V _{GS} = -10V, R _{GEN} =3Ω		20		nS
Turn-on Rise Time	T _r			13		
Turn-off Delay Time	T _{d(off)}			55		
Turn-off Fall Time	T _f			21		
Total Gate Charge	Q _g	V _{DS} = -15V, I _D = -10A , V _{GS} = -10V		65		nC
Gate-Source Charge	Q _{gs}			12		
Gate-Drain Charge	Q _{gd}			14		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S = -15A			-1.2	V

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Characteristics

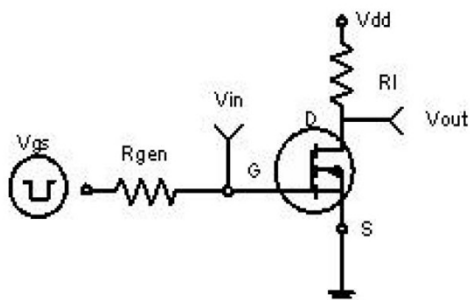


Figure 1 Switching Test Circuit

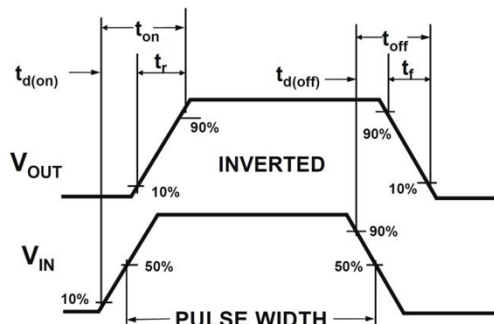


Figure 2 Switching Waveforms

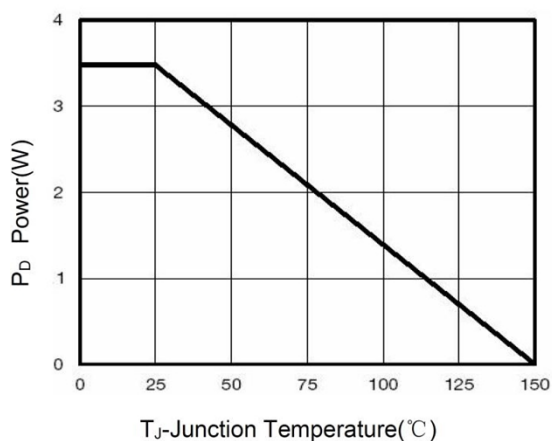


Figure 3 Power Dissipation

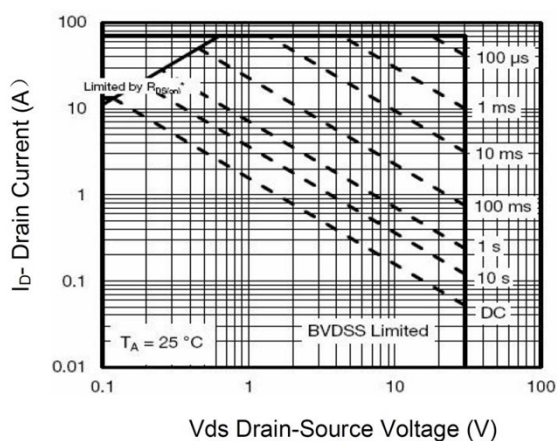


Figure 4 Safe Operation Area

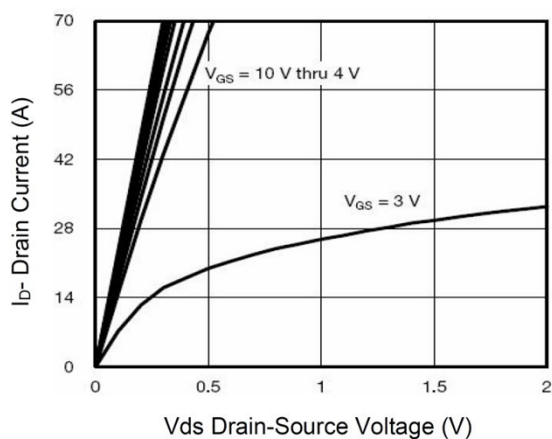


Figure 5 Output Characteristics

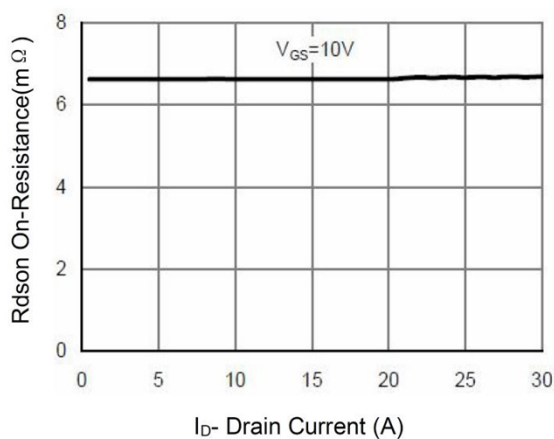


Figure 6 Drain-Source On-Resistance

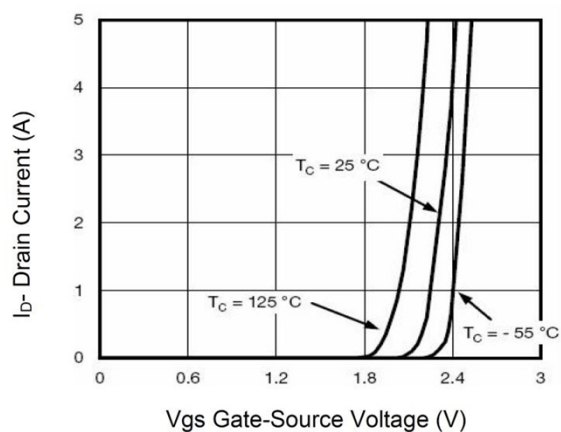


Figure 7 Transfer Characteristics

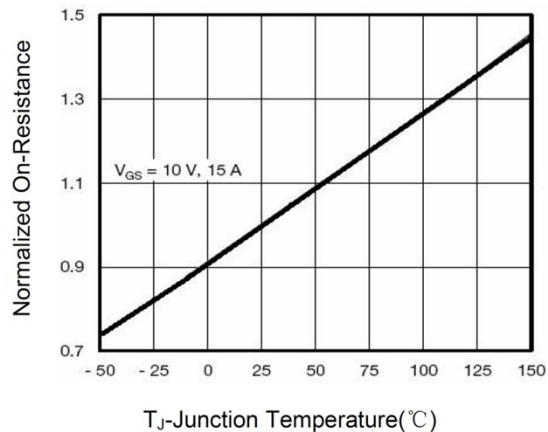


Figure 8 Drain-Source On-Resistance

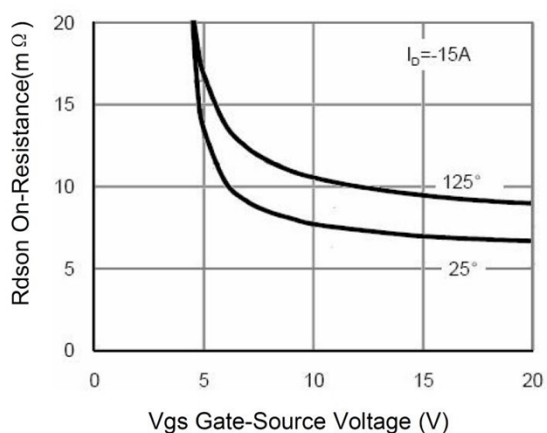


Figure 9 Rdson vs Vgs

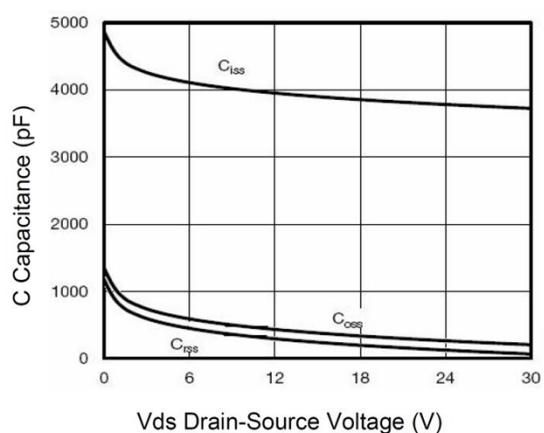


Figure 10 Capacitance vs Vds

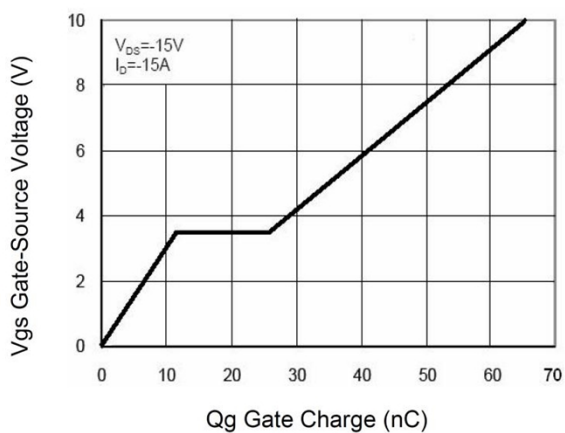


Figure 11 Gate Charge

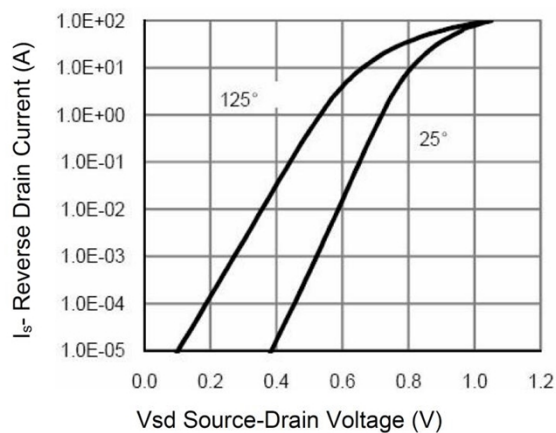


Figure 12 Source- Drain Diode Forward

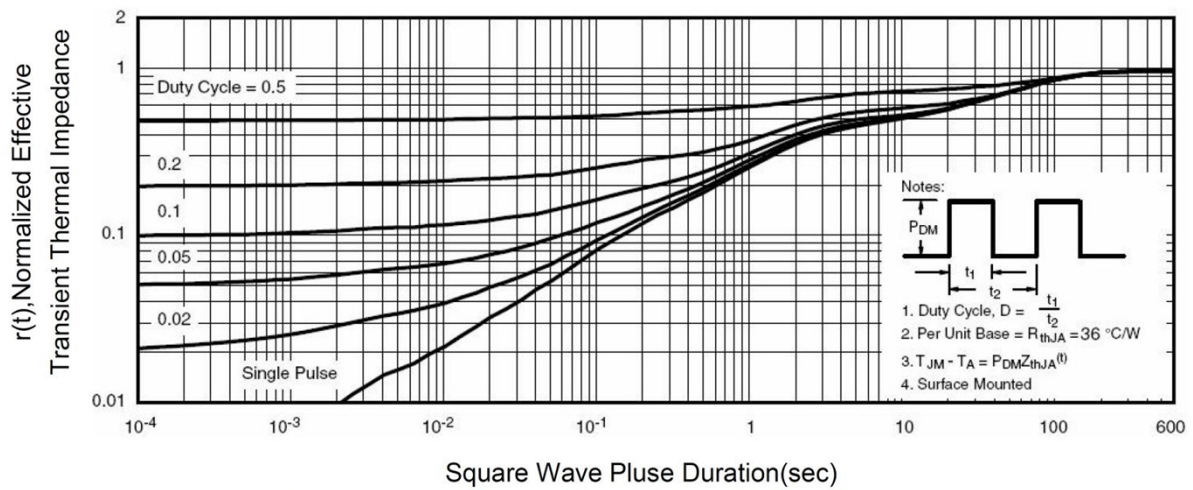
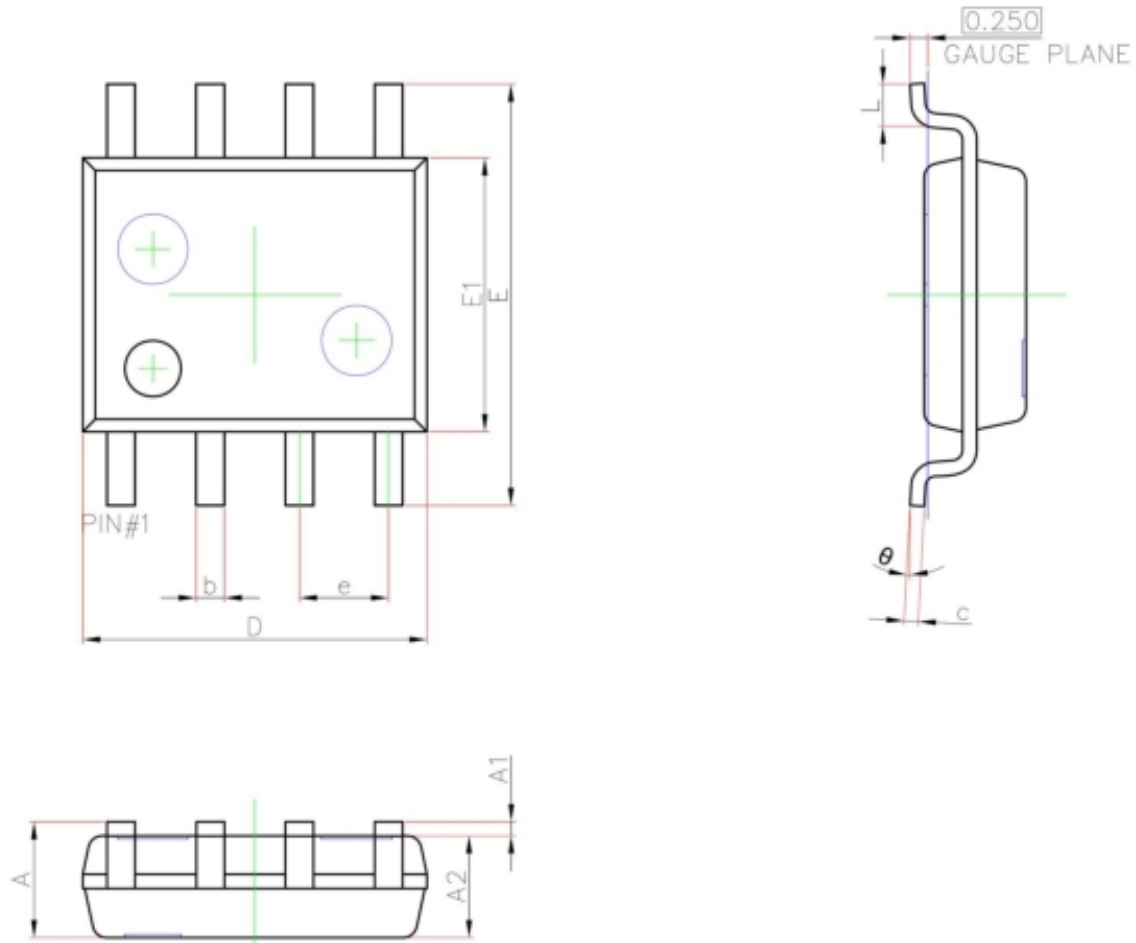


Figure 13 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.450	1.750	0.057	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°